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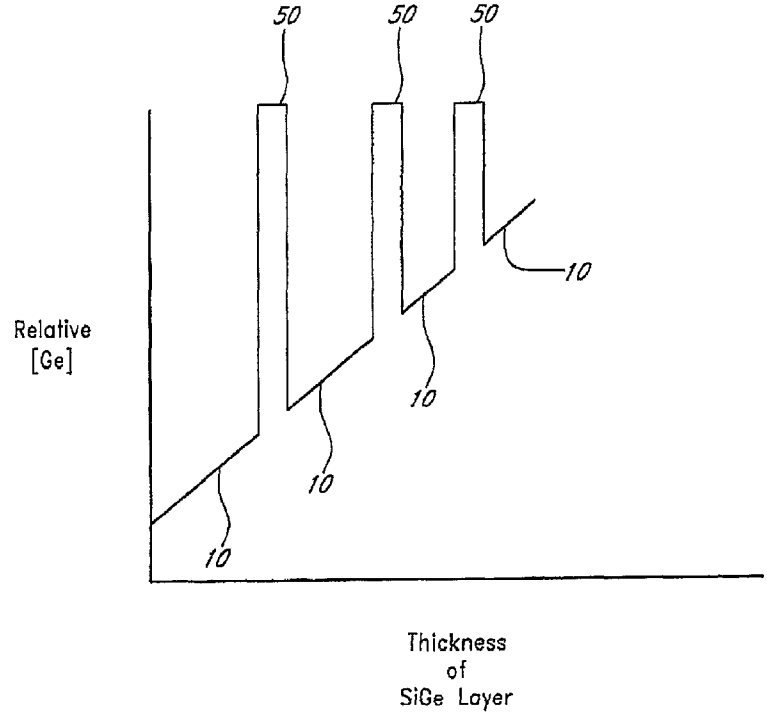
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(54) Title: SEMICONDUCTOR BUFFER STRUCTURES



(57) Abstract: Pile ups of threading dislocations in thick graded buffer layer are reduced by enhancing dislocation gliding. During formation of a graded SiGe buffer layer, deposition of SiGe from a silicon precursor and a germanium precursor is interrupted one or more times with periods in which the flow of the silicon precursor to the substrate is stopped while the flow of the germanium precursor to the substrate is maintained.

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